

a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,

a pixel electrode,

a thin film transistor connected to one of the data lines and one of

the gate lines defining the cell,

a storage capacitor, and

a metallic pattern having drain electrode of the thin film transistor and a storage electrode of the storage capacitor, and being electrically connected to the pixel electrode.

2. (Amended) The liquid crystal device of claim 1, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.

3. (Amended) The liquid crystal device of claim 2, further comprising:
a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

4. (Amended) The liquid crystal device of claim 1, further comprising:
a protective layer disposed between the pixel electrode and the metallic pattern, and wherein
a portion of a periphery of the pixel electrode overlaps the metallic pattern.

5. (Amended) The liquid crystal device of claim 4, wherein
the metallic pattern has an annular shape, and
an entire periphery of the pixel electrode overlaps the metallic pattern.

6. (Amended) The liquid crystal device of claim 5, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.

7. (Amended) The substrate of claim 1, further comprising:
a protective layer disposed between the pixel electrode and the metallic pattern, and wherein
the pixel electrode is connected to a storage electrode part of the metallic pattern via a first contact hole in the protective layer.

8. (Amended) The liquid crystal device of claim 7, wherein the protective layer does not include a contact hole over a drain electrode part of the metallic pattern.

Del B2 9. (Amended) The liquid crystal device of claim 8, wherein the drain electrode part has a smaller area than if the drain electrode part was electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.

a1 10. (Amended) The liquid crystal device of claim 8, wherein the pixel electrode has a larger aspect ratio than if the drain electrode part was electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.

11. (Amended) The liquid crystal device of claim 8, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and a portion of a periphery of the pixel electrode overlaps the metallic pattern.

12. (Amended) The liquid crystal device of claim 8, wherein the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

13. (Amended) The liquid crystal device of claim 7, wherein the pixel electrode is connected to a drain electrode part of the metallic pattern via a second contact hole in the protective layer.

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14. (Amended) The liquid crystal device of claim 13, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and a portion of a periphery of the pixel electrode overlaps the metallic pattern.

15. (Amended) The liquid crystal device of claim 13, wherein the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and an entire periphery of the pixel electrode overlaps the metallic pattern.

16. (Amended) The liquid crystal device of claim 1, further comprising:
a protective layer disposed between the pixel electrode and the metallic
pattern, and wherein

the pixel electrode is connected to a drain electrode part of the metallic
pattern via a contact hole in the protective layer.

17. (Amended) The liquid crystal device of claim 16, wherein the
protective layer does not include a contact hole over a storage electrode part of
a the metallic pattern.

~~18. (Amended) The liquid crystal device of claim 17, wherein the pixel
electrode overlaps a gate line, defining the cell but not connected to the thin
film transistor, less than if the protective layer included a contact hole over a
storage electrode part of the metallic pattern.~~

19. (Amended) The liquid crystal device of claim 17, wherein
the metallic pattern is spaced a predetermined distance from the data
line connected to the thin film transistor; and
a portion of a periphery of the pixel electrode overlaps the metallic
pattern.

20 20. (Amended) The liquid crystal device of claim 16, wherein
the metallic pattern has an annular shape and is spaced a
predetermined distance from the data line connected to the thin film transistor;
and
an entire periphery of the pixel electrode overlaps the metallic pattern.

Sub By 21. (Amended) A liquid crystal device having a thin film transistor,
comprising:

21 a plurality of gate lines formed on a substrate;
a plurality of data lines insulated from and intersecting said gate lines,
said data lines and intersecting gate lines defining a plurality of cells, at least
one cell including,
a pixel electrode,
a thin film transistor selectively electrically connecting one of the
data lines to the pixel electrode, and including a source electrode connected to
the one of the data lines, a gate electrode connected to one of the gate lines,
and a drain electrode, and
a storage capacitor having a storage electrode and a drain
electrode, the storage capacitor being connected to the pixel electrode.

22. (Amended) The liquid crystal device of claim 21, wherein the storage electrode and the drain electrode are connected to each other by a metallic pattern.

23. (Amended) A method of manufacturing a thin film transistor substrate, comprising:

forming a gate line having a gate electrode on a transparent substrate;

forming a gate insulating layer on the gate electrode;

forming a semiconductor layer on the gate insulating layer;

forming a data line having a source electrode, and a metallic pattern having a drain electrode part and a storage electrode part;

forming a semiconductor layer over at least a portion of one of the gate electrodes, at least a portion of one of the source electrode, and at least a portion of the drain electrode part;

forming a protective film over the entire surface; and

forming a pixel electrode over the protective film.

24. (Amended) The method of claim 23, wherein the forming the data line and the metallic pattern step is performed simultaneously by forming a conductive layer over the substrate and patterning the conductive layer to form

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Cont. the data line and the metallic pattern such that the metallic pattern is spaced a predetermined distance from the data line.

Q2 27. (Amended) The method of claim 23, wherein the forming a protective layer step forms the protective layer with a first contact hole exposing the storage electrode part of the metallic pattern.

Q3 31. (Amended) The method of claim 30, wherein the forming a protective layer step does not form the protective layer with a contact hole exposing the storage electrode part of the metallic pattern.

REMARKS

Claims 1-31 are pending in the present application. Claims 1, 21 and 23 are independent. Claims 1-24, 27 and 31 are amended by this response.

The Applicant appreciates the Examiner's indication that claims 5, 12, 15, 20 and 26 contain allowable subject matter.

The drawings stand objected to under 37 CFR 1.83(a) as not showing every feature of the invention specified in the claims. Claim 7 has been amended so that it no longer recites "a pixel electrode being connected to a source electrode, but recites a storage electrode in the place where a source electrode was recited previously.